



- 1 Batchwise preparation.
- 2 Typical spectral response of a photodiode.

ACTIVE SILICON SSP865 PHOTODIODE TECHNOLOGY

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General information

The Fraunhofer IPMS photo sensors are PIN-like diodes with both contacts (diode, substrate) at the wafer front side.

The combination of the Fraunhofer IPMS photodiode technology with typical MEMS devices (grooves, slits) enables the development and fabrication of specific solutions for optical measurement systems.

Technical Data

Parameter	Value	Condition
Spectral responsivity	typ. 0.64	at 865 nm, 2.5 V
Dark current	typ. 0.05 nA/mm ² typ. 5 nA/mm ²	27 °C, 2.5 V 125 °C, 2.5 V
Temperature range	-40 °C – 125 °C	
Capacitance	max. 10 pF/mm ²	27 °C, 2.5 V, 100 Hz
Cut-off frequency	typ. 800 kHz	27 °C, 2.5 V, 865 nm
Shunt resistance	min. 2 MΩ	1 mm ² , 125 °C, 0.1 V

